

*B/* *can.* 5 a passivation film covering the surface of the semiconductor substrate and the wirings, including a first insulating film that contains a [at least one impurity selected from the group consisting of argon,] boron impurity [, nitrogen and phosphorus].

*Sub* *can.* 26. (As filed) The semiconductor device according to claim 25, wherein the passivation film includes a second insulating film, located on at least one of an upper side and a lower side of the first insulating film, having a hygroscopicity lower than that of the first insulating film.

*Sub* *can.* 27. (As filed) The semiconductor device according to claim 26, wherein the second insulating film is selected from the group consisting of silicon nitride film, silicon oxide film and silicon oxynitride film.

*Sub* *can.* 28. (Amended) The semiconductor device according to claim 25, wherein organic components in the first insulating film have been decomposed by said boron [the at least one selected] impurity.

*Sub* *can.* 29. (As filed) The semiconductor device according to claim 28, wherein the passivation film includes a second insulating film, located on at least one of an upper side and a lower side of the first insulating film, having a hygroscopicity lower than that of the first insulating film.

*Sub* *can.* 30. (As filed) The semiconductor device according to claim 29, wherein the second insulating film is selected from the group consisting of silicon nitride film, silicon oxide film and silicon oxynitride film.

*Sub* *can.* 31. (As filed) The semiconductor device according to claim 25, wherein the first insulating film includes an inorganic SOG (Spin-on-Glass) film.

*Sub* *can.* 32. (As filed) The semiconductor device according to claim 31, wherein the passivation film includes a second insulating film, located on at least one of an upper side and a lower side of the first insulating film, having a hygroscopicity lower than that of the first insulating film.